

## REMARKS

Claims 1-36 are pending in the application.

Claims 1-36 are rejected.

Claim 20 is objected to. Claim 20 is amended to replace the term “dependant” with “dependent.” Thus, the claim objection is overcome.

Applicant respectfully thanks The Examiner for accepting the drawings filed on February 20, 2002.

Applicant respectfully thanks The Examiner for acknowledging foreign priority claim under 35 U.S.C. § 119(a)–(d).

Claims 20 and 22 are amended.

No new matter is added.

Claims 1-36 remain in the case.

Applicant requests reconsideration and allowance of the claims in light of the above amendments and following remarks.

### **Claim Rejections – 35 USC § 102**

Claims 1-36 are rejected under 35 U.S.C. 102(e) as being anticipated by U.S. Patent No. 6,489,252 B2 issued to Goo et al. (“Goo”).

The rejections are respectfully traversed.

Goo fails to teach or disclose, “chemical mechanical polishing the insulating film and exposing an upper portion of the wiring pattern,” as claimed in independent claim 1.

On the contrary, Goo merely teaches, at column 5, lines 39-45, forming an oxide layer or a silicon nitride layer before applying a polysilazane SOG layer. Thus, Goo does not teach all of the limitations of claim 1.

Furthermore, in Goo, an insulation layer 57 comprising polysilazane is directly coated on a substrate 51 on which patterns 53 are formed. In contrast, in the claimed invention, an insulation layer 18 comprising polysilazane is formed on the polished insulation layer 14, not on the substrate 10 as in Goo. See, for example, the specification at page 10, lines 18-30 of the present application. Compare FIG. 6 of Goo with FIG. 10 of the present application.

Therefore, nowhere does Goo teach or disclose,

“chemical mechanical polishing the insulating film and exposing an upper portion of the wiring pattern;

coating the polished insulation and exposed portion of the wiring pattern with spin on glass composition to form a film;

the coating using polysilazane in the spin on glass composition,” as recited in claim 1 of the present application.

Therefore, claims 1 and claims 2-19, which depend therefrom, are allowable. Also, for the reasons discussed above, claims 20 and 21, which recite similar limitations to claim 1, are allowable.

Also, with respect to the rejections of claims 22-36, claim 22 is amended to recite, “coating a spin on glass composition on a first insulation film that is formed on semiconductor substrate having a conductive pattern, the conductive pattern being exposed through the first insulation film, the coating using polysilazane in the spin on glass composition; curing the spin on glass composition to form a second insulation film; outgassing the second insulation film, the outgassing comprising releasing silane gas; and annealing and oxidizing the second insulation film.”

The Examiner has not pointed to specific teachings of any of the prior art regarding the various claim limitations of claim 22.

For these reasons, Goo does not anticipate claim 22. Also, claims 23-36, which depend from allowable claim 22 and recite features that are neither taught nor disclosed in the cited references, are also allowable.

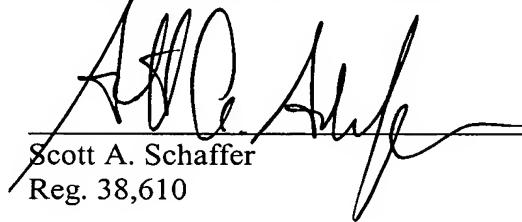
## **CONCLUSION**

For the foregoing reasons, reconsideration and allowance of claims 1-36 of the application as amended is solicited. The Examiner is encouraged to telephone the undersigned at (503) 222-3613 if it appears that an interview would be helpful in advancing the case.

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Respectfully submitted,

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